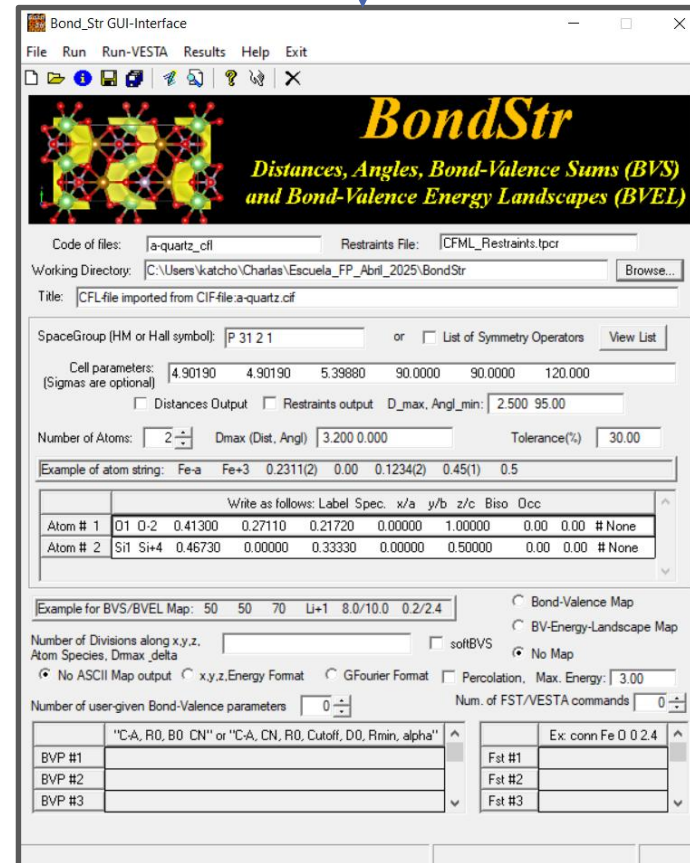
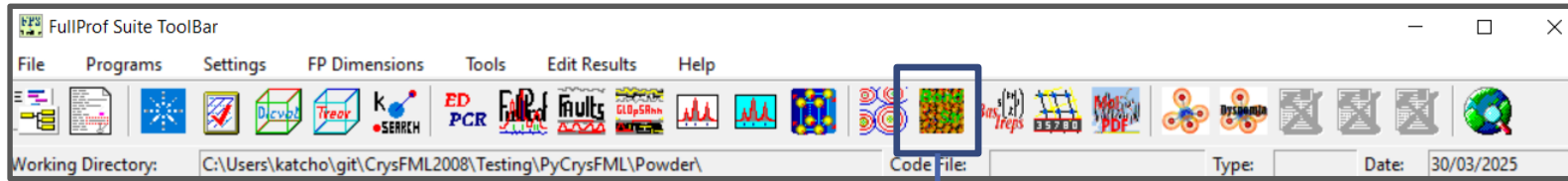


The program BondStr: an implementation of bond-valence theory

The Graphical User Interface of BondStr



Pauling rules

- **Pauling rules** are a series of structural principles for ionic compounds.

First rule: Coordination polyhedral

A coordination polyhedron of anions is formed around every cation. The cation-anion distances are determined by the sum of the ionic radii, and the coordination number of the cation by the radius ratio.

Second rule: The electrostatic valence rule

In a stable ionic structure the valence (ionic charge) of each anion with changed sign is exactly or nearly equal to the sum of the electrostatic bond strengths to it from adjacent cations. The electrostatic bond strength is defined as the ratio of the charge on a cation to its coordination number.

Bond strengths: calculation

s_i : bond strength for cation i

q_{i+} : atomic charge (valence) of cation i

n_{i+} : coordination number of cation i

q_{j-} : atomic charge (valence) of anion j

n_{j-} : coordination number of anion j



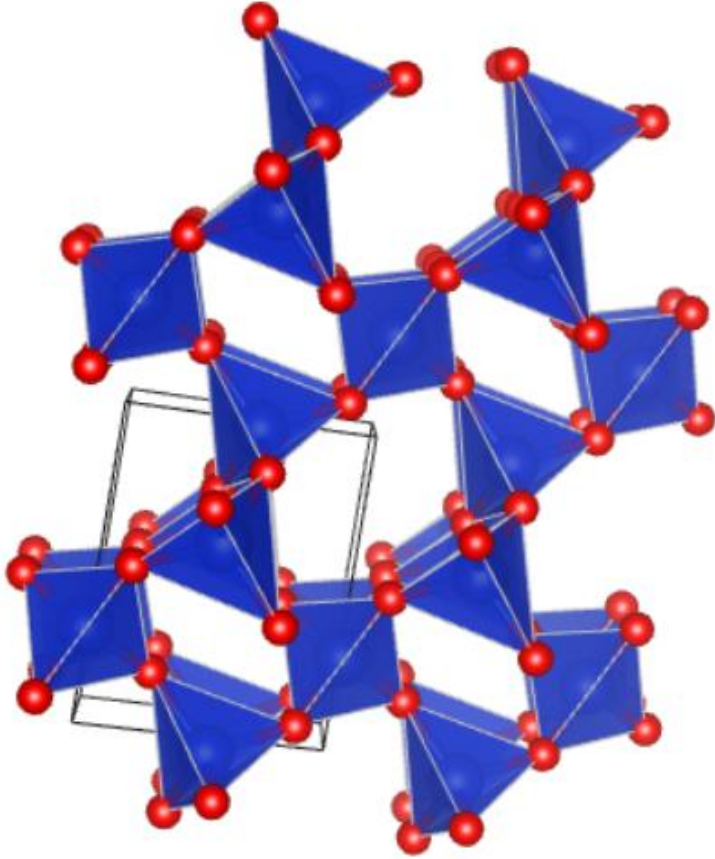
$$s_i = \frac{q_{i+}}{n_{i+}}$$



$$q_{j-} = \sum_{i=1}^{n_{j-}} s_i$$

Bond strengths: an example

α -SiO₂ (quartz)



$$q_{Si} = +4; n_{Si} = 4; n_O = 2$$



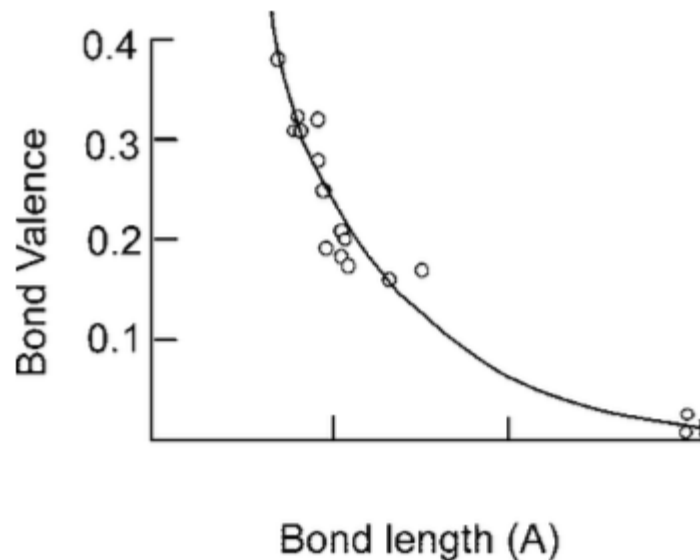
$$s_{Si} = \frac{q_{Si}}{n_{Si}} = \frac{4}{4} = 1$$



$$q_O = - \sum_{i=1}^2 s_i = -1 - 1 = -2$$

Basics of bond-valence theory

- The bond-valence theory is a development of the **Pauling rules**.
- Each bond A-X has a bond strength s_{A-X} , which depends on bond length, chemical nature of the elements and oxidation states.



$$s_{A-X} = \exp\left(\frac{R_0 - R_{A-X}}{b}\right)$$

R_0 and b ($\approx 0.37\text{\AA}$) are tabulated parameters characteristic of the pair A-X and R_{A-X} is the bond length

<http://www.iucr.org/resources/data/data-sets/bond-valence-parameters>

I. D. Brown, *The Chemical Bond in Inorganic Chemistry: The Bond Valence Model*, Oxford University Press, 2002.

The bond-valence sum

- **Valence sum rule:** The total valence V_A of the cation A (ideally equal to the magnitude of the formal charge) coordinated by N anions X is given by the bond-valence sum (**BVS**):

$$V_A = \sum_{i=1}^{N_C} s_{A-X_i} \approx V_A^{ideal} (formal\ charge)$$



Atomic valences can be computed from bond distances

Validation of crystal structures

- The bond valence approach is frequently used to validate newly determined crystal structures by the calculation of the **Global Instability Index (GII)**

$$GII^2 = \frac{1}{N_{cell}} \sum_{i=1}^{N_{asym}} m_i (BVS_i - V_i^{ideal})^2$$

N_{cell} : total number of atoms in the unit cell

N_{asym} : number of atoms in the asymmetric unit

m_i : multiplicity of the site i .

- In stable, well determined structures, theGII is usually less than **0.1** valence units. Values between **0.1**and **0.2** indicate a strained structure, whereas higher values are unusual and can point to an incorrect structure determination.

An example: α -SiO₂

=> Bond-valence and coordination of atom: O1 occupancy: 1.000(0)

```
(O1 )-(Si1 ) : 1.6073( 0) 1.046( 0)
(O1 )-(Si1 ) : 1.6161( 0) 1.022( 0)
```

individual bond strengths

```
Coordination number:      2      Eff.Coor. number: 2.00 for atom: O1
Average distance  : 1.6117( 0) Distortion: 0.074 xE-04
Predicted distance: 1.6240
```

```
Single bond-valence S= 1.000
valence: -2.000
Sums: 2.068( 0)
```

bond-valence sum

```
Deviation from the valence Sum Rule (r1,%dev): 0.068 3.390
{r1=Sumj(sij)-Vi, %dev=100abs(r1)/Vi}
Deviation from the Equal valence Rule (r2): 0.012
{r2=<sij-<sij>>rms}
```

=> Bond-valence and coordination of atom: Si1 occupancy: 1.000(0)

```
(Si1 )-(O1 ) : 1.6073( 0) 1.046( 0)
(Si1 )-(O1 ) : 1.6161( 0) 1.022( 0)
(Si1 )-(O1 ) : 1.6074( 0) 1.046( 0)
(Si1 )-(O1 ) : 1.6158( 0) 1.022( 0)
```

individual bond strengths

```
Coordination number:      4      Eff.Coor. number: 4.00 for atom: Si1
Average distance  : 1.6117( 0) Distortion: 0.070 xE-04
Predicted distance: 1.6240
```

```
Single bond-valence S= 1.000
valence: 4.000
Sums: 4.136( 0)
```

bond-valence sum

```
Deviation from the valence Sum Rule (r1,%dev): 0.136 3.398
{r1=Sumj(sij)-Vi, %dev=100abs(r1)/Vi}
Deviation from the Equal valence Rule (r2): 0.012
{r2=<sij-<sij>>rms}
```

An example: α -SiO₂

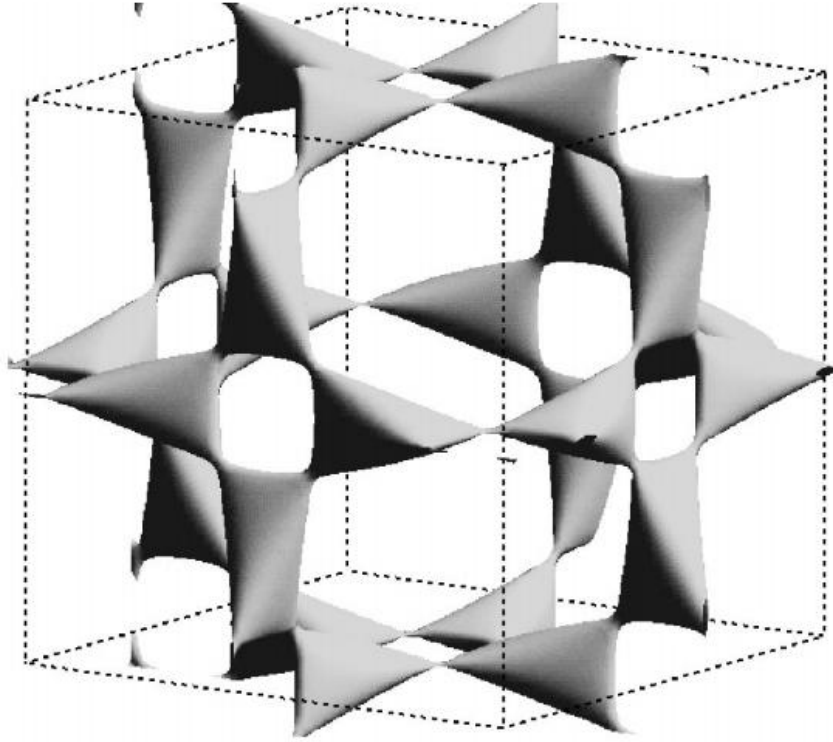
=> The old Global Instability Index (GII) is calculated with the atoms of the asymmetric unit (Num_Atoms). The normalized GII(a,b,c) below are calculated using the sum over asymmetric unit but multiplying differences by the multiplicity of the site. N_Atoms_UCell is the total number of atoms in the conventional unit cell. In all cases the result of the different expressions is multiplied by 100.0

```
=> Old Global Instability Index ( GII=SQRT{SUM{|BVS-abs(q)|^2}/Num_Atoms} ) = 10.74 /100
=> Normalized GII(a)= SUM {|BVS-abs(q)| *mult}/N_Atoms_UCell = 9.05 /100
=> Normalized GII(b)= SUM {|BVS-abs(q)| *mult/abs(q)}/N_Atoms_UCell = 3.39 %
=> Normalized GII(c)= SQRT{ SUM {|BVS-abs(q)|^2*mult}/N_Atoms_UCell}= 9.60 /100
=> Summary of BVS in File: a-quartz_cfl_sum.bvs
```

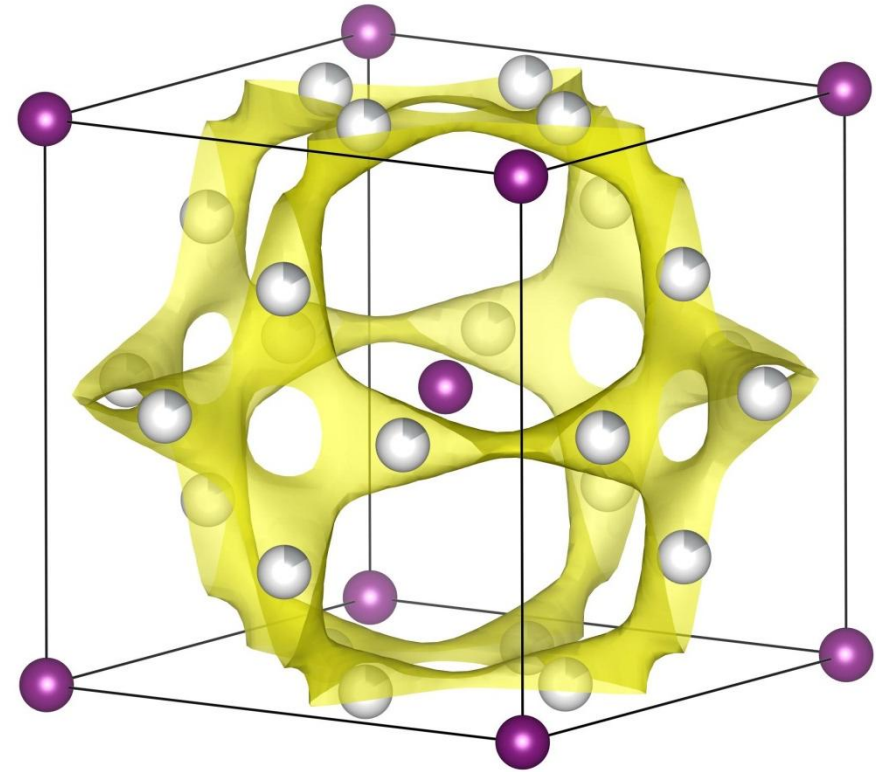
Ionic conductivity

- The bond-valence method can be used for assessing the ionic conduction path from the knowledge of the crystal structure.
- Low-energy transport pathways for the motion of ions between equilibrium sites **should correspond to a sequence of positions for which the BVS mismatch: $\Delta V(r) = |BVS(r) - V^{\text{ideal}}(r)|$ remain as small as possible**, so a simple geometric calculation allows to figure out possible ionic conduction paths.

Bond-valence mismatch



Bond-valence isosurface
for α -AgI ($\Delta V=0.05$ val. un.)

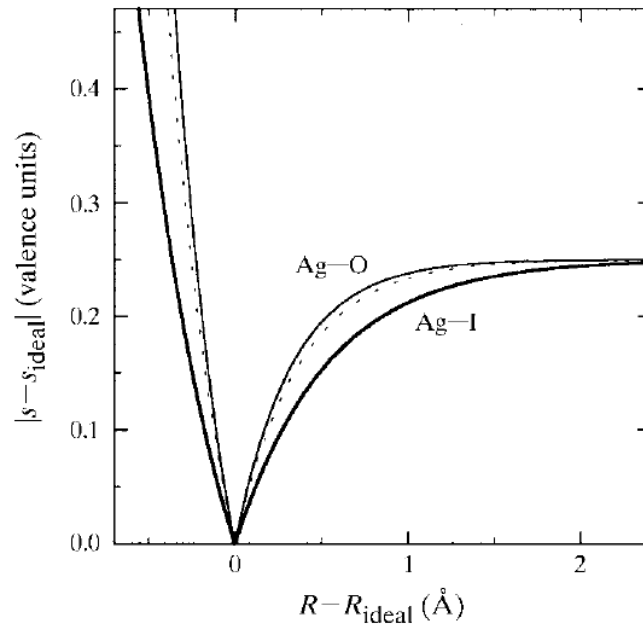


Bond valence isosurface
for α -AgI ($\Delta V=0.083$ val. un.)

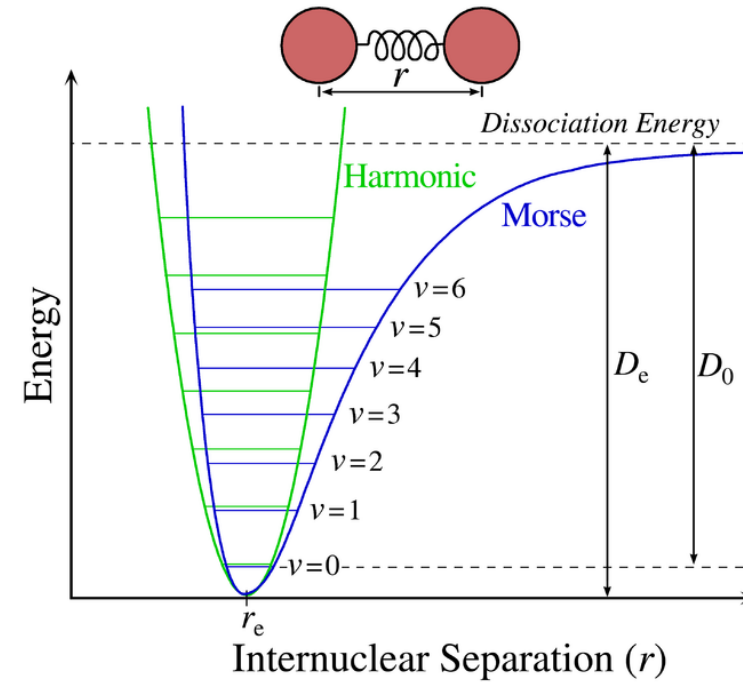
S. Adams, J. Swenson, Phys. Rev. B 63 (2000) 054201

Bond-valence energy landscape

Pseudopotential representation of the correlation between bond-length R and bond valence s .



Typical Morse potential



S. Adams, Acta Cryst. B 57 (2001) 278

Bond-valence energy landscape

Stefan Adams, *Practical Considerations in Determining Bond-Valence Parameters, Structure and Bonding* **158**, 91-128 (2014)

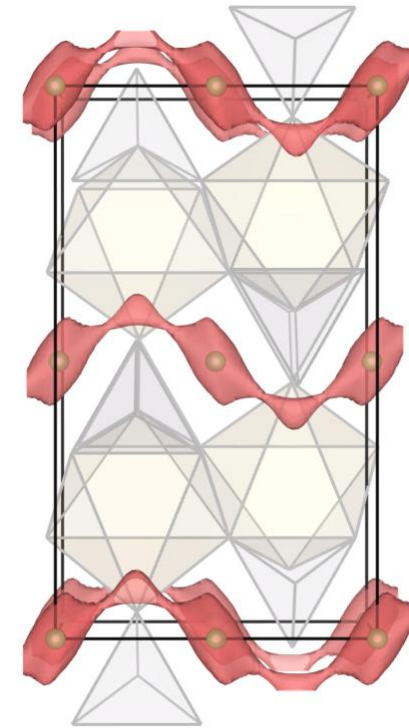
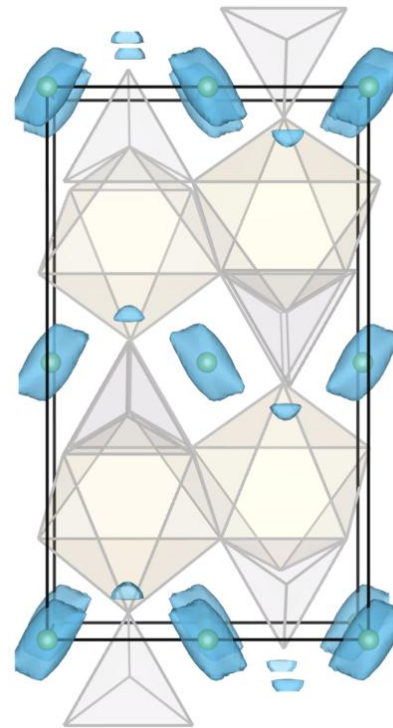
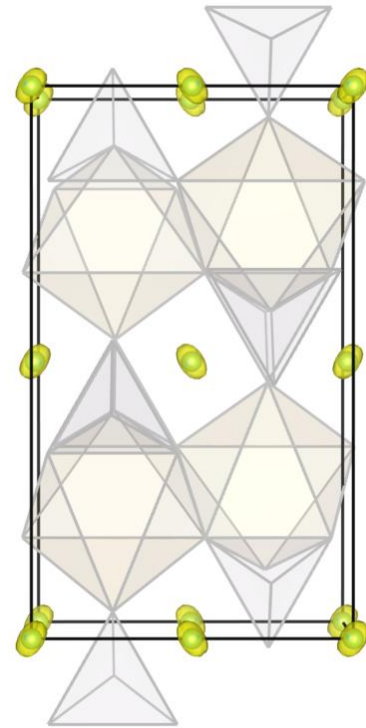
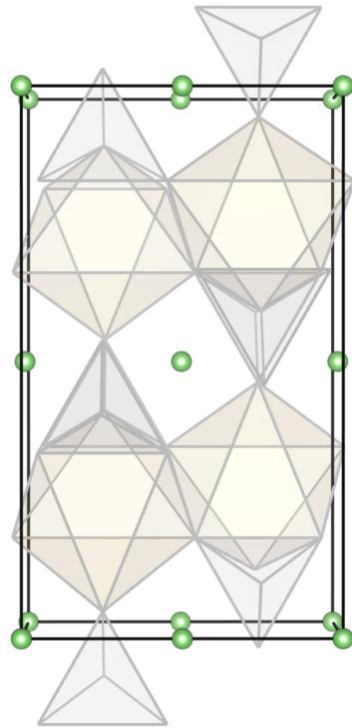
$$E = D_0 \left\{ (\exp[\alpha(R_{\min} - R)] - 1)^2 - 1 \right\}$$
$$= D_0 \left\{ \left(\frac{\exp\left[\frac{R_0 - R}{b}\right] - s_{\min}}{s_{\min}} \right)^2 - 1 \right\}$$

$$\text{BVSE}(\text{M}) = D_0 \left[\sum_{j=1}^{N_X} \frac{(s_{\text{M-X}_j} - s_{\min})^2}{s_{\min}^2} - N \right] + \sum_{i=1}^{N_M} E_{\text{Coulomb}}(\text{M} - \text{M}_i)$$

$$E_{\text{Coulomb}}(\text{M}_1 - \text{M}_2) = \frac{q_{\text{M}_1} q_{\text{M}_2}}{R_{\text{M}_1 - \text{M}_2}} \operatorname{erfc} \left(\frac{R_{\text{M}_1 - \text{M}_2}}{\rho_{\text{M}_1 - \text{M}_2}} \right)$$

An example: LiFePO_4

Energy isosurfaces of LiFePO_4

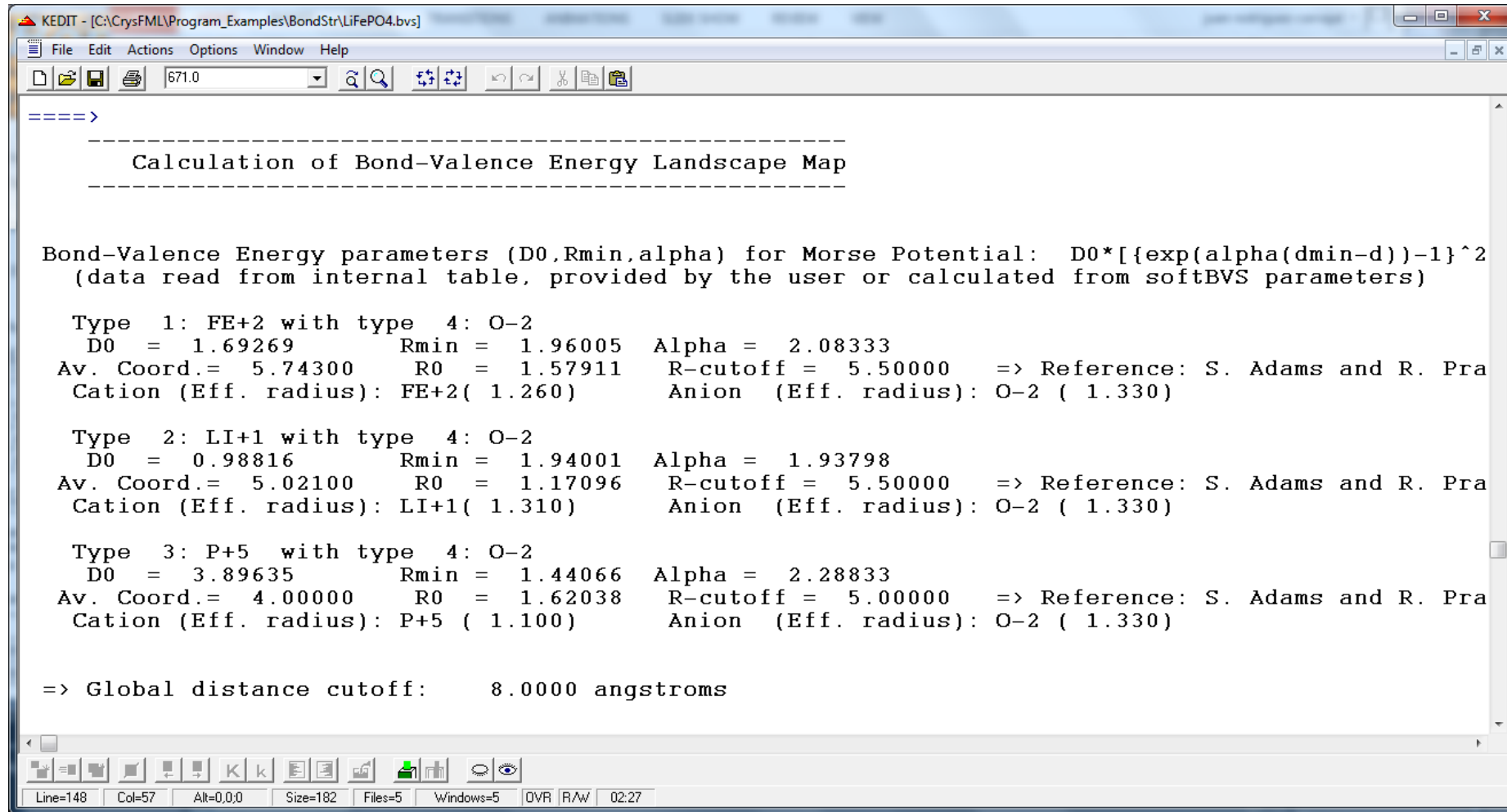


$$E - E_{\min} = 0.20 \text{ eV}$$

$$E - E_{\min} = 0.80 \text{ eV}$$

$$E - E_{\min} = 0.91 \text{ eV}$$

An example: LiFePO_4



KEDIT - [C:\CrysFML\Program_Examples\BondStr\LiFePO4.bvs]

File Edit Actions Options Window Help

671.0

====>

Calculation of Bond-Valence Energy Landscape Map

Bond-Valence Energy parameters (D0,Rmin,alpha) for Morse Potential: $D0 * [\exp(\alpha(d_{\min} - d)) - 1]^2$
(data read from internal table, provided by the user or calculated from softBVS parameters)

Type 1: FE+2 with type 4: O-2
D0 = 1.69269 Rmin = 1.96005 Alpha = 2.08333
Av. Coord.= 5.74300 R0 = 1.57911 R-cutoff = 5.50000 => Reference: S. Adams and R. Pra
Cation (Eff. radius): FE+2(1.260) Anion (Eff. radius): O-2 (1.330)

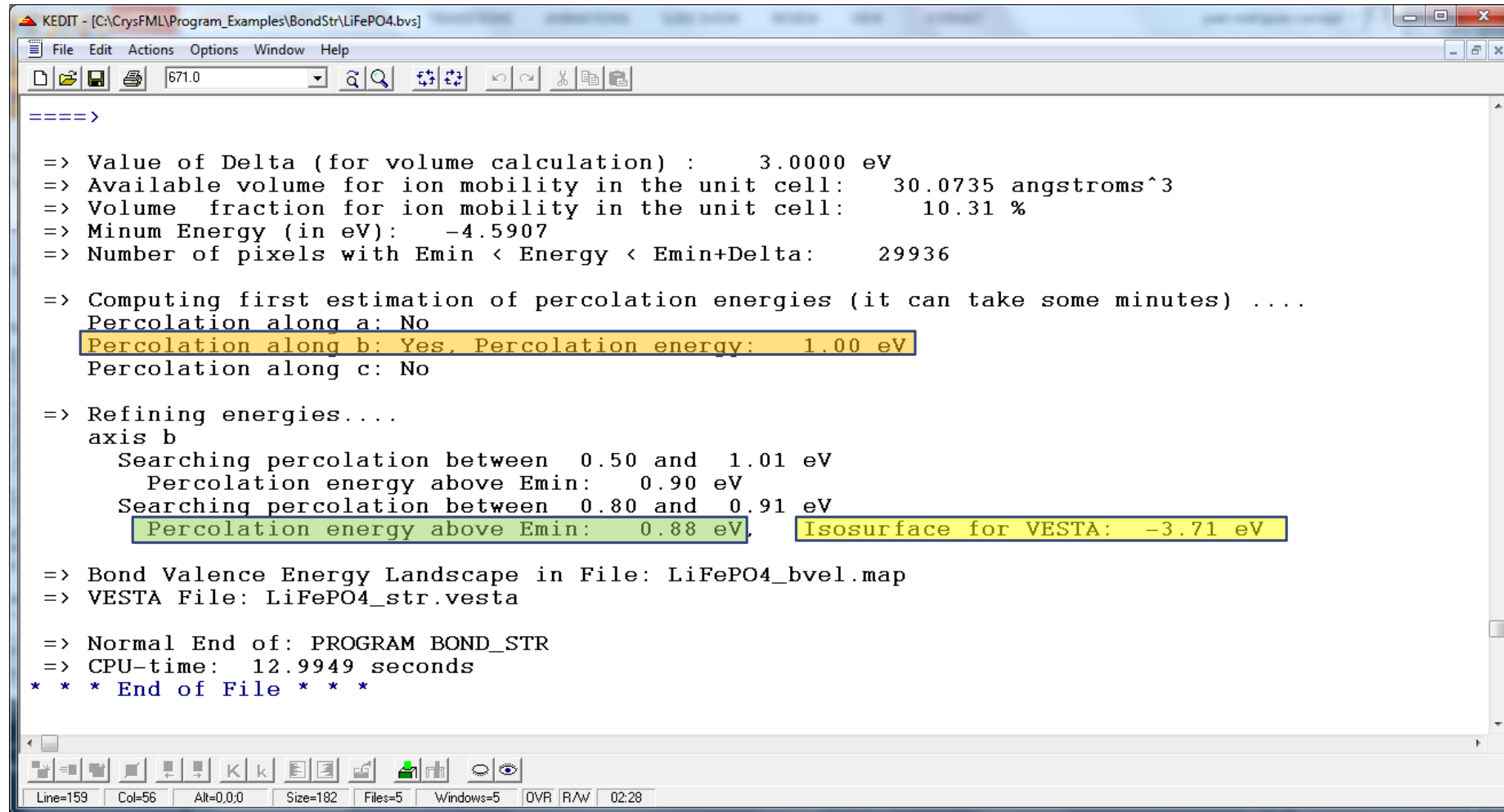
Type 2: LI+1 with type 4: O-2
D0 = 0.98816 Rmin = 1.94001 Alpha = 1.93798
Av. Coord.= 5.02100 R0 = 1.17096 R-cutoff = 5.50000 => Reference: S. Adams and R. Pra
Cation (Eff. radius): LI+1(1.310) Anion (Eff. radius): O-2 (1.330)

Type 3: P+5 with type 4: O-2
D0 = 3.89635 Rmin = 1.44066 Alpha = 2.28833
Av. Coord.= 4.00000 R0 = 1.62038 R-cutoff = 5.00000 => Reference: S. Adams and R. Pra
Cation (Eff. radius): P+5 (1.100) Anion (Eff. radius): O-2 (1.330)

=> Global distance cutoff: 8.0000 angstroms

Line=148 Col=57 Alt=0,0,0 Size=182 Files=5 Windows=5 OVR R/W 02:27

An example: LiFePO_4



```
KEDIT - [C:\CrysFML\Program_Examples\BondStr\LiFePO4.bvs]
File Edit Actions Options Window Help
671.0
====>
=> Value of Delta (for volume calculation) : 3.0000 eV
=> Available volume for ion mobility in the unit cell: 30.0735 angstroms^3
=> Volume fraction for ion mobility in the unit cell: 10.31 %
=> Minum Energy (in eV): -4.5907
=> Number of pixels with Emin < Energy < Emin+Delta: 29936

=> Computing first estimation of percolation energies (it can take some minutes) ....
Percolation along a: No
Percolation along b: Yes, Percolation energy: 1.00 eV
Percolation along c: No

=> Refining energies....
axis b
Searching percolation between 0.50 and 1.01 eV
Percolation energy above Emin: 0.90 eV
Searching percolation between 0.80 and 0.91 eV
Percolation energy above Emin: 0.88 eV, Isosurface for VESTA: -3.71 eV

=> Bond Valence Energy Landscape in File: LiFePO4_bvel.map
=> VESTA File: LiFePO4_str.vesta

=> Normal End of: PROGRAM BOND_STR
=> CPU-time: 12.9949 seconds
* * * End of File * * *
```

BVEL vs DFT

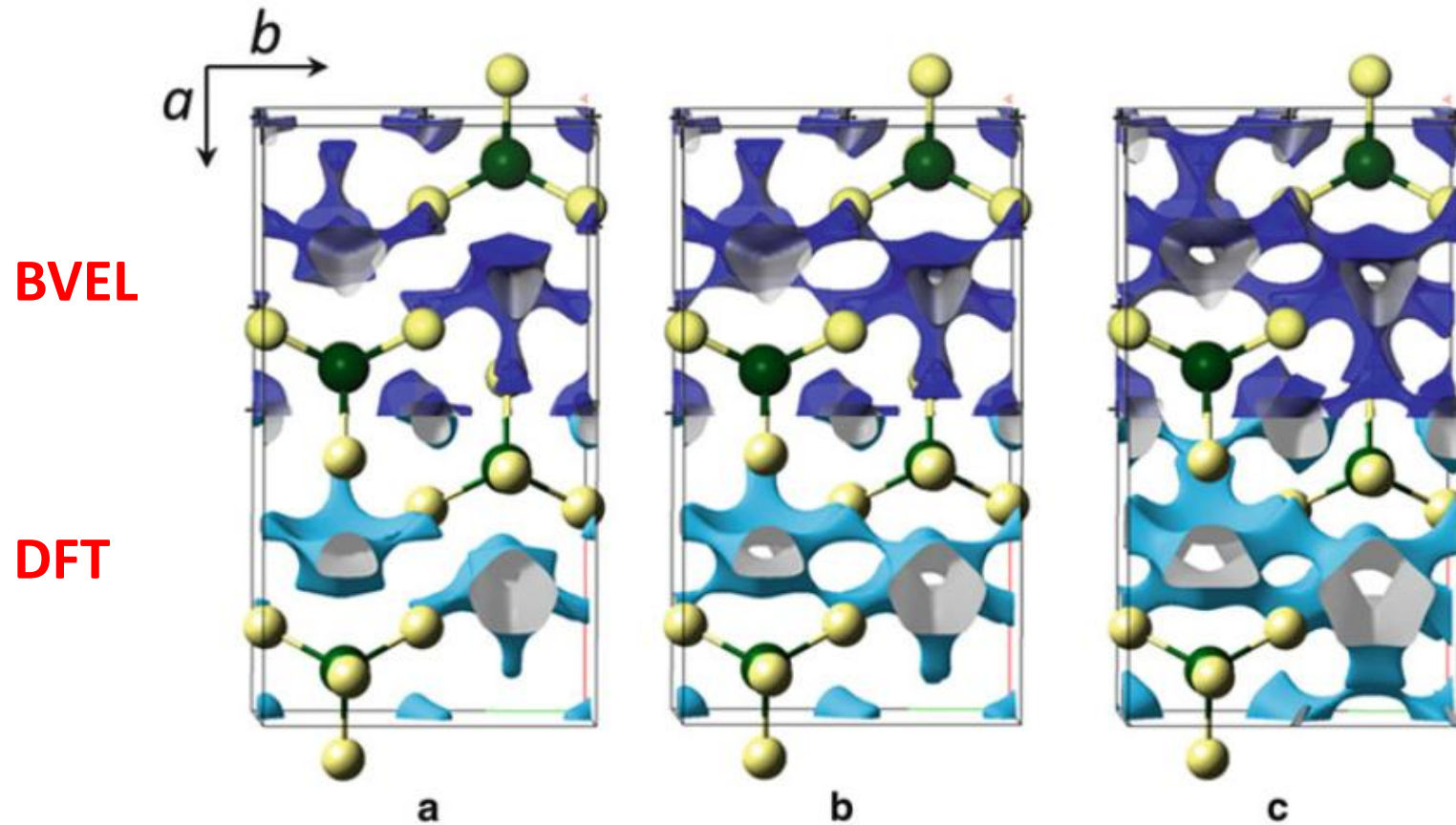


Fig. 12 Regions in the Li_4GeS_4 structure accessible to moving Li^+ ions according to BVSE energy calculations (*top half* of the unit cell) for ΔE_{BVSE} of (a) 0.95 eV, (b) 1.1 eV and (c) 1.35 eV and the procrystal analysis (*bottom half* of the unit cell) showing paths with electron density isovalues of 0.0016 au, 0.0018 au, and 0.0024 au, respectively

Summary

- Bond-Valence Energy maps/isosurfaces give a clear evidence (first approximation) for the ionic diffusion pathways in the material
- **BVEL Model** has a high predictive potential and is adapted for studying whatever ionic diffusion species
 - the cation conductors, e.g. sodium or magnesium
 - the anion conductors, e.g. oxygen or hydrogen ...
- The **BVEL Model is restricted to compounds close to ionic character**; e.g. it does not, in general, apply to metals or organic compounds